TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7MA573FK

Low-Voltage Octal D-Type Latch with 3.6 V Tolerant Inputs and Outputs

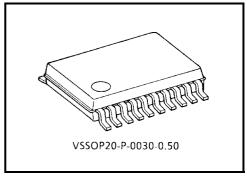
The TC7MA573FK is a high performance CMOS octal D-type latch. Designed for use in 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to  $3.6\ V.$ 

This 8 bit D-type latch is controlled by a latch enable input (LE) and an output enable input ( $\overline{OE}$ ).

When the  $\overline{\mbox{OE}}$  input is high, the eight outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.03 g (typ.)

#### **Features**

- Low voltage operation: V<sub>CC</sub> = 1.8~3.6 V
- High speed operation:  $t_{pd} = 4.2 \text{ ns (max) (VCC} = 3.0 \sim 3.6 \text{ V)}$

 $t_{pd} = 4.7 \text{ ns (max) (VCC} = 2.3~2.7 \text{ V)}$ 

 $t_{pd} = 9.4 \text{ ns (max) (VCC} = 1.8 \text{ V)}$ 

- 3.6 V tolerant inputs and outputs.
- Output current:  $I_{OH}/I_{OL} = \pm 24 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

 $IOH/IOL = \pm 18 \text{ mA (min) (VCC} = 2.3 \text{ V)}$ 

 $IOH/IOL = \pm 6 \text{ mA (min) (VCC} = 1.8 \text{ V)}$ 

- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200

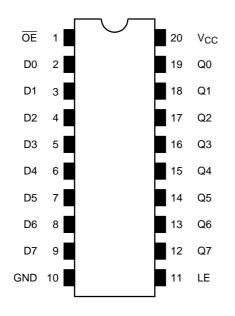
Human body model  $> \pm 2000 \text{ V}$ 

- Package: VSSOP (US20)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (\*)

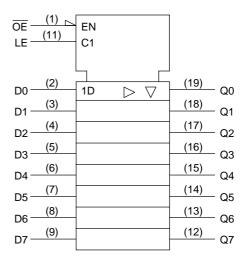
1

<sup>\*:</sup> To ensure the high-impedance state during power up or power down,  $\overline{\sf OE}$  should be tied to V<sub>CC</sub> through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

# Pin Assignment (top view)



# **IEC Logic Level**



#### **Truth Table**

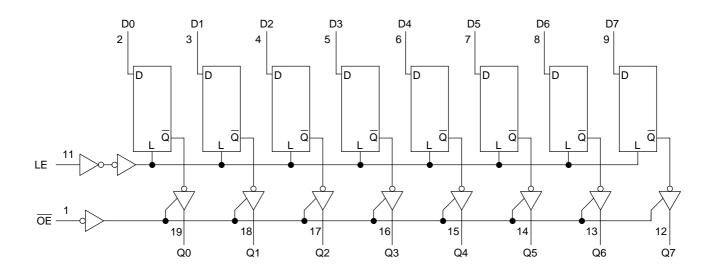
	Inputs	Outputs	
ŌĒ	LE	D	Odipaio
Н	Х	X	Z
L	L	Х	Q <sub>n</sub>
L	Н	L	L
L	Н	Н	Н

X: Don't care

Z: High impedance

Q<sub>n</sub>: Q outputs are latched at the time when the LE inputs is taken to a low logic level.

### **System Diagram**



2



### **Maximum Ratings**

Characteristics	Symbol	Rating	Unit
Power supply voltage	V <sub>CC</sub>	-0.5~4.6	V
DC input voltage	V <sub>IN</sub>	-0.5~4.6	V
DC output voltage	V	-0.5~4.6 (Note1)	V
DC output voltage	V <sub>OUT</sub>	-0.5~V <sub>CC</sub> + 0.5 (Note2)	V
Input diode current	I <sub>IK</sub>	-50	mA
Output diode current	I <sub>OK</sub>	±50 (Note3)	mA
DC output current	I <sub>OUT</sub>	±50	mA
Power dissipation	PD	180	mW
DC V <sub>CC</sub> /ground current	I <sub>CC</sub> /I <sub>GND</sub>	±100	mA
Storage temperature	T <sub>stg</sub>	-65~150	°C

Note1: Off-state

Note2: High or low state.  $I_{\mbox{\scriptsize OUT}}$  absolute maximum rating must be observed.

Note3:  $V_{OUT} < GND, V_{OUT} > V_{CC}$ 

# **Recommended Operating Range**

Characteristics	Symbol	Rating	Unit
Supply voltage	V	1.8~3.6	V
Supply voltage	V <sub>CC</sub>	1.2~3.6 (Note4)	V
Input voltage	V <sub>IN</sub>	-0.3~3.6	V
Output voltage	\/	0~3.6 (Note5)	V
Output voltage	Vout	0~V <sub>CC</sub> (Note6)	V
		±24 (Note7)	
Output current	I <sub>OH</sub> /I <sub>OL</sub>	±18 (Note8)	mA
		±6 (Note9)	
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note10)	ns/V

Note4: Data retention only

Note5: Off-state

Note6: High or low state

Note7:  $V_{CC} = 3.0 \sim 3.6 \text{ V}$ 

Note8:  $V_{CC} = 2.3 \sim 2.7 \text{ V}$ 

Note9:  $V_{CC} = 1.8 \text{ V}$ 

Note10:  $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$ 

3

### **Electrical Characteristics**

**TOSHIBA** 

# DC Characteristics (Ta = $-40 \sim 85$ °C, 2.7 V < V<sub>CC</sub> $\leq$ 3.6 V)

Characteri	stics	Symbol	Test Condition		V <sub>CC</sub> (V)	Min	Max	Unit
Input voltage	High level	V <sub>IH</sub>		_	2.7~3.6	2.0	_	V
input voitage	Low level	V <sub>IL</sub>		_	2.7~3.6	_	0.8	V
				I <sub>OH</sub> = -100 μA	2.7~3.6	V <sub>CC</sub> - 0.2		
	High level	V <sub>OH</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$	I <sub>OH</sub> = -12 mA	2.7	2.2	_	
				$I_{OH} = -18 \text{ mA}$	3.0	2.4	_	
Output voltage				$I_{OH} = -24 \text{ mA}$	3.0	2.2	_	V
		level V <sub>OL</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 100 \mu A$	2.7~3.6		0.2	
1 1	Low level			$I_{OL} = 12 \text{ mA}$	2.7	_	0.4	
	LOW level			$I_{OL} = 18 \text{ mA}$	3.0		0.4	
				$I_{OL} = 24 \text{ mA}$	3.0		0.55	
Input leakage curre	nt	I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		2.7~3.6		±5.0	μΑ
3-state output off-st	tate output off-state current $I_{OZ}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0  3.6 \text{ V}$			2.7~3.6	_	±10.0	μΑ	
Power off leakage of	current	l <sub>OFF</sub>	V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0	_	10.0	μА
	Quiescent supply current		V <sub>IN</sub> = V <sub>CC</sub> or GND		2.7~3.6	_	20.0	
Quiescent supply co			$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.$	CC ≦ (V <sub>IN</sub> , V <sub>OUT</sub> ) ≦ 3.6 V			±20.0	μΑ
		Δlcc	$V_{IH} = V_{CC} - 0.6 V$ (per	input)	2.7~3.6	_	750	

# DC Characteristics (Ta = $-40\sim85^{\circ}$ C, 2.3 V $\leq$ V<sub>CC</sub> $\leq$ 2.7 V)

Characte	ristics	Symbol	Test Condition		V <sub>CC</sub> (V)	Min	Max	Unit			
	High level	V <sub>IH</sub>			2.3~2.7	1.6	_				
Input voltage	Low level	V <sub>IL</sub>		_	2.3~2.7	_	0.7	V			
				$I_{OH} = -100 \mu A$	2.3~2.7	V <sub>CC</sub> - 0.2	_				
	High level	Voh	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -6 mA	2.3	2.0	_				
						I <sub>OH</sub> = -12 mA	2.3	1.8	_		
Output voltage	voltage			I <sub>OH</sub> = -18 mA	2.3	1.7	_	V			
			$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 100 \mu A$	2.3~2.7	_	0.2				
	Low level	$V_{OL}$		$V_{IN} = V_{IH} \ or \ V_{IL}$	$V_{IN} = V_{IH} \ or \ V_{IL}$	$V_{IN} = V_{IH} \ or \ V_{IL}$	I <sub>OL</sub> = 12 mA	2.3		0.4	
				I <sub>OL</sub> = 18 mA	2.3		0.6				
Input leakage curr	ent	I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		2.3~2.7		±5.0	μΑ			
2 state output off o	2 state output off state ourrent		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$			110.0	^			
3-state output off-state current		loz	V <sub>OUT</sub> = 0~3.6 V	V <sub>OUT</sub> = 0~3.6 V			±10.0	μА			
Power off leakage	current	loff	V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0	_	10.0	μΑ			
Quioscont supply	ourront	loo	$V_{IN} = V_{CC}$ or GND	V <sub>IN</sub> = V <sub>CC</sub> or GND		_	20.0	^			
Quiescent supply	current	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le$	3.6 V	2.3~2.7	_	±20.0	μА			

# DC Characteristics (Ta = $-40~85^{\circ}$ C, 1.8 V $\leq$ V<sub>CC</sub> < 2.3 V)

Characteris	stics	Symbol	Test Condition		V <sub>CC</sub> (V)	Min	Max	Unit						
la mada and la ma	High level	V <sub>IH</sub>		_		0.7 × V <sub>CC</sub>	_							
Input voltage	Low level	V <sub>IL</sub>		_	1.8~2.3	_	0.2 × V <sub>CC</sub>	V						
	High level	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -100 μA	1.8	V <sub>CC</sub> - 0.2	_							
Output voltage		0		I <sub>OH</sub> = -6 mA	1.8	1.4	_	V						
	Low level	.,	\/-· \	V <sub>OL</sub> V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 100 μA	1.8	_	0.2						
	Low level	VOL	VIN — VIH OI VIL	$I_{OL} = 6 \text{ mA}$	1.8		0.3							
Input leakage currer	nt	I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		1.8		±5.0	μΑ						
3-state output off-sta	output off-state current I <sub>OZ</sub>		$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = 0 \sim 3.6 \text{ V}$		1.8	_	±10.0	μА						
Power off leakage c	urrent	I <sub>OFF</sub>	V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0	_	10.0	μΑ
Ouissant supply supply		laa	$V_{IN} = V_{CC}$ or GND	V <sub>IN</sub> = V <sub>CC</sub> or GND		_	20.0	μА						
Quiescent supply cu	<u></u>	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8	_	±20.0	μΑ						

5 2001-10-23

# AC Characteristics (Ta = $-40 \sim 85$ °C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ $\Omega$ )

Characteristics	Symbol	Test Condition		Min	Max	Unit
			V <sub>CC</sub> (V)			
	t <sub>pLH</sub>	E. 4 E. 0	1.8	1.5	9.4	
Propagation delay time (D-Q)	t <sub>pHL</sub>	Figure 1, Figure 2	2.5 ± 0.2	0.8	4.7	ns
			$3.3 \pm 0.3$	0.6	4.2	
	t <sub>pLH</sub>		1.8	1.5	9.8	
Propagation delay time (LE-Q)	tpHL	Figure 1, Figure 2	$2.5\pm0.2$	8.0	4.9	ns
	-priL		$3.3 \pm 0.3$	0.6	4.2	
			1.8	1.5	9.8	
3-state output enable time	t <sub>pZL</sub>	Figure 1, Figure 3	$2.5\pm0.2$	0.8	5.5	ns
	t <sub>pZH</sub>		$3.3 \pm 0.3$	0.6	4.5	
		Figure 1, Figure 3	1.8	1.5	6.5	ns
3-state output disable time	t <sub>pLZ</sub>		$2.5\pm0.2$	0.8	3.6	
	t <sub>pHZ</sub>		$3.3 \pm 0.3$	0.6	3.3	
			1.8	4.0	_	
Minimum pulse width	t <sub>w (H)</sub>	t <sub>w (H)</sub> Figure 1, Figure 2		1.5	_	ns
			$3.3 \pm 0.3$	1.5	_	
			1.8	2.5	_	
Minimum set-up time	ts	Figure 1, Figure 2	$2.5\pm0.2$	1.5	_	ns
			$3.3 \pm 0.3$	1.5	_	
			1.8	1.0	_	
Minimum hold time	t <sub>h</sub>	Figure 1, Figure 2	$2.5\pm0.2$	1.0	_	ns
			$3.3 \pm 0.3$	1.0	_	
			1.8	_	0.5	
Output to output skew	t <sub>osLH</sub>	(Note11)	$2.5 \pm 0.2$	_	0.5	ns
	t <sub>osHL</sub>		$3.3 \pm 0.3$	_	0.5	

For  $C_L = 50\ pF$ , add approximately 300 ps to the AC maximum specification.

Note11: This parameter is guaranteed by design.

 $(t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)$ 

# Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition	Vc	C (V)	Тур.	Unit
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12)	1.8	0.25	
Quiet output maximum dynamic V <sub>OL</sub>	$V_{OLP}$	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Not	12)	2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Not	12)	3.3	0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12)	1.8	-0.25	V
Quiet output minimum dynamic V <sub>OL</sub>	$V_{OLV}$	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Not	12)	2.5	-0.6	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Not	12)	3.3	-0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12)	1.8	1.5	
Quiet output minimum dynamic VOH	$V_{OHV}$	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Not	12)	2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Not	12)	3.3	2.2	

Note12: This parameter is guaranteed by design.

### **Capacitive Characteristics (Ta = 25°C)**

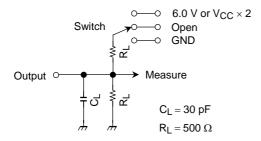
Characteristics	Symbol	Test Condition			Тур.	Unit
Characteristics	Syllibol			V <sub>CC</sub> (V)	τyp.	Offic
Input capacitance	C <sub>IN</sub>	_		1.8, 2.5, 3.3	6	pF
Output capacitance	CO	_		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C <sub>PD</sub>	f <sub>IN</sub> = 10 MHz	(Note13)	1.8, 2.5, 3.3	20	pF

Note13: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$ 

#### **AC Test Circuit**



Parameter	Switch		
t <sub>pLH</sub> , t <sub>pHL</sub>	Open		
t <sub>pLZ</sub> , t <sub>pZL</sub>			
t <sub>pHZ</sub> , t <sub>pZH</sub>	GND		

Figure 1

#### **AC Waveform**

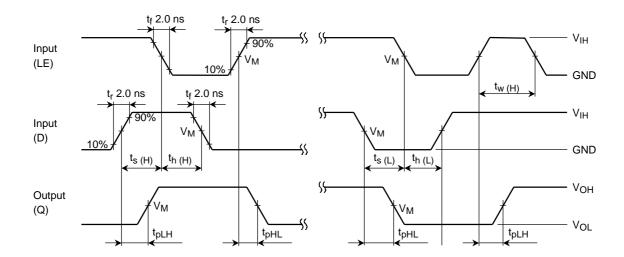


Figure 2  $t_{pLH}, t_{pHL}, t_w, t_s, t_h$ 

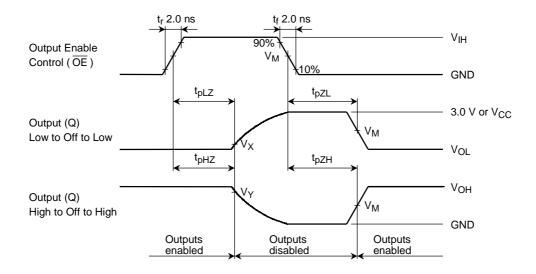


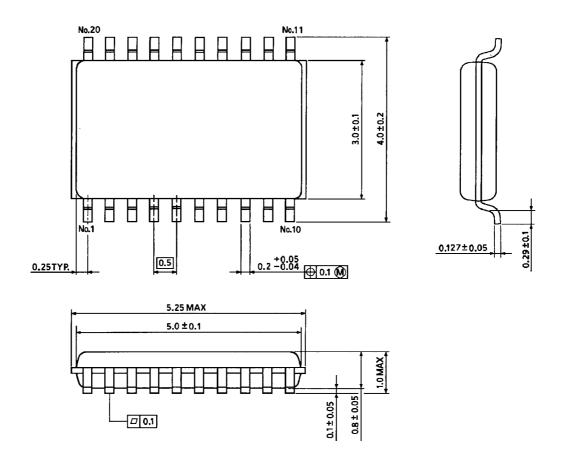
Figure 3  $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$ 

Symbol	V <sub>CC</sub>						
Symbol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V				
V <sub>IH</sub>	2.7 V	V <sub>CC</sub>	V <sub>CC</sub>				
$V_{M}$	1.5 V	V <sub>CC</sub> /2	V <sub>CC</sub> /2				
V <sub>X</sub>	V <sub>OL</sub> + 0.3 V	V <sub>OL</sub> + 0.15 V	V <sub>OL</sub> + 0.15 V				
VY	V <sub>OH</sub> – 0.3 V	V <sub>OH</sub> – 0.15 V	V <sub>OH</sub> – 0.15 V				

9 2001-10-23

# **Package Dimensions**

**TOSHIBA** 



Weight: 0.03 g (typ.)

#### RESTRICTIONS ON PRODUCT USE

000707EBA

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
  In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.